

N-channel 650 V, 0.090 Ω typ., 22.5 A MDmesh™ M5 Power MOSFET in a PowerFLAT™ 8x8 HV package

Datasheet - production data

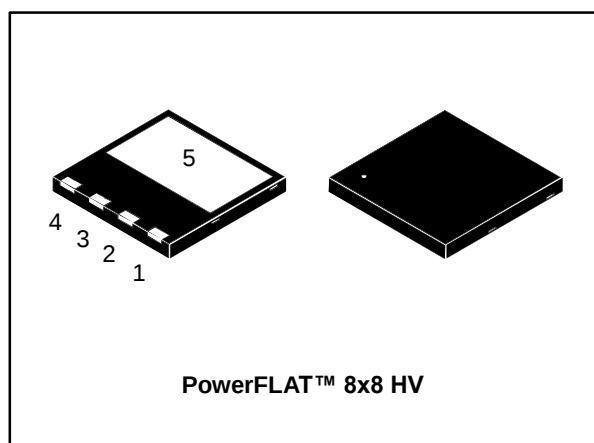
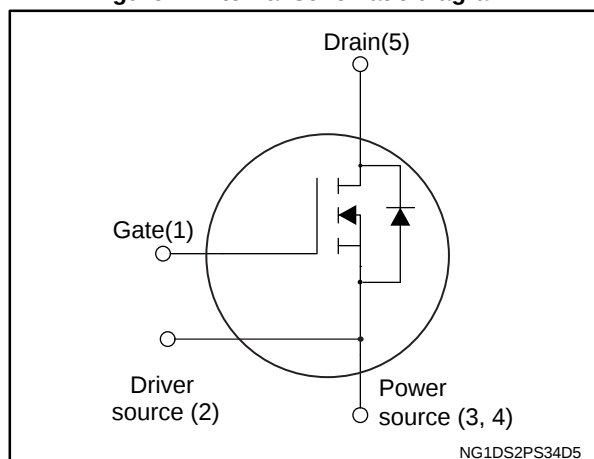


Figure 1: Internal schematic diagram



Features

Order code	V _{DS} @ T _{Jmax}	R _{DS(on)} max.	I _D
STL38N65M5	710 V	0.105 Ω	22.5 A

- Extremely low R_{DS(on)}
- Low gate charge and input capacitance
- Excellent switching performance
- 100% avalanche tested

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET based on the MDmesh™ M5 innovative vertical process technology combined with the well-known PowerMESH™ horizontal layout. The resulting product offers extremely low on-resistance, making it particularly suitable for applications requiring high power and superior efficiency.

Table 1: Device summary

Order code	Marking	Package	Packaging
STL38N65M5	38N65M5	PowerFLAT™ 8x8 HV	Tape and reel

Contents

1	Electrical ratings	3
2	Electrical characteristics	4
2.1	Electrical characteristics (curves).....	6
3	Test circuits	9
4	Package information	10
4.1	PowerFLAT™ 8x8 HV package information.....	11
4.2	PowerFLAT™ 8x8 HV packing information.....	13
5	Revision history	15

1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	650	V
V_{GS}	Gate-source voltage	± 25	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	22.5	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	16	A
$I_{DM}^{(1)(2)}$	Drain current (pulsed)	90	A
$I_D^{(3)}$	Drain current (continuous) at $T_{pcb} = 25\text{ }^\circ\text{C}$	3.5	A
$I_D^{(3)}$	Drain current (continuous) at $T_{pcb} = 100\text{ }^\circ\text{C}$	2.2	A
$P_{TOT}^{(3)}$	Total dissipation at $T_{pcb} = 25\text{ }^\circ\text{C}$	2.8	W
$P_{TOT}^{(4)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	150	W
I_{AR}	Avalanche current, repetitive or notrepetitive (pulse width limited by T_j max)	7	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	660	mJ
$dv/dt^{(4)}$	Peak diode recovery voltage slope	15	V/ns
T_{stg}	Storage temperature	- 55 to 150	$^\circ\text{C}$
T_j	Max. operating junction temperature	150	

Notes:

⁽¹⁾The value is rated according to $R_{thj-case}$.

⁽²⁾Pulse width limited by safe operating area.

⁽³⁾When mounted on FR-4 board of 1 inch², 2oz Cu.

⁽⁴⁾ $I_{SD} \leq 22.5\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$; $V_{DS(peak)} < V_{(BR)DSS}$, $V_{DD} = 400\text{ V}$.

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.83	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max	45	$^\circ\text{C}/\text{W}$

Notes:

⁽¹⁾When mounted on FR-4 board of 1 inch², 2oz Cu.

2 Electrical characteristics

$T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Table 4: On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	650			V
I_{DSS}	Zero gate voltage Drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 650\text{ V}$			1	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 650\text{ V}$, $T_C = 125\text{ }^{\circ}\text{C}$			100	μA
I_{GSS}	Gate-body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 25\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 12.5\text{ A}$		0.090	0.105	Ω

Table 5: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	3000	-	pF
C_{oss}	Output capacitance		-	74	-	pF
C_{rss}	Reverse transfer capacitance		-	5.8	-	pF
$C_{o(er)}^{(1)}$	Equivalent output capacitance energy related	$V_{DS} = 0\text{ to }80\% V_{(BR)DSS}$, $V_{GS} = 0\text{ V}$	-	70	-	pF
$C_{o(tr)}^{(2)}$	Equivalent output capacitance time related		-	244	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$	-	2.4	-	Ω
Q_g	Total gate charge	$V_{DD} = 520\text{ V}$, $I_D = 15\text{ A}$, $V_{GS} = 10\text{ V}$ (see Figure 16 : "Gate charge test circuit")	-	71	-	nC
Q_{gs}	Gate-source charge		-	18	-	nC
Q_{gd}	Gate-drain charge		-	30	-	nC

Notes:

⁽¹⁾ $C_{o(er)}$ is defined as a constant equivalent capacitance giving the same stored energy as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

⁽²⁾ $C_{o(tr)}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 6: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(V)}$	Voltage delay time	$V_{DD} = 400\text{ V}$, $I_D = 20\text{ A}$ $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 17 : "Test circuit for inductive load switching and diode recovery times" and Figure 20 : "Switching time waveform")	-	66	-	ns
$t_{r(V)}$	Voltage rise time		-	9	-	ns
$t_{f(i)}$	Crossing fall time		-	9	-	ns
$t_{c(off)}$	Crossing time		-	13	-	ns

Table 7: Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}^{(1)}$	Source-drain current		-		22.5	A
$I_{SDM}^{(1),(2)}$	Source-drain current (pulsed)		-		90	A
$V_{SD}^{(3)}$	Forward on voltage	$V_{GS} = 0\text{ V}$, $I_{SD} = 22.5\text{ A}$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 22.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 100\text{ V}$ (see Figure 17 : "Test circuit for inductive load switching and diode recovery times")	-	354		ns
Q_{rr}	Reverse recovery charge		-	6		μC
I_{RRM}	Reverse recovery current		-	34		A
t_{rr}	Reverse recovery time	$I_{SD} = 22.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 100\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$ (see Figure 17 : "Test circuit for inductive load switching and diode recovery times")	-	428		ns
Q_{rr}	Reverse recovery charge		-	8		μC
I_{RRM}	Reverse recovery current		-	38		A

Notes:

⁽¹⁾The value is rated according to $R_{thj-case}$ and limited by package.

⁽²⁾Pulse width is limited by safe operating area

⁽³⁾Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

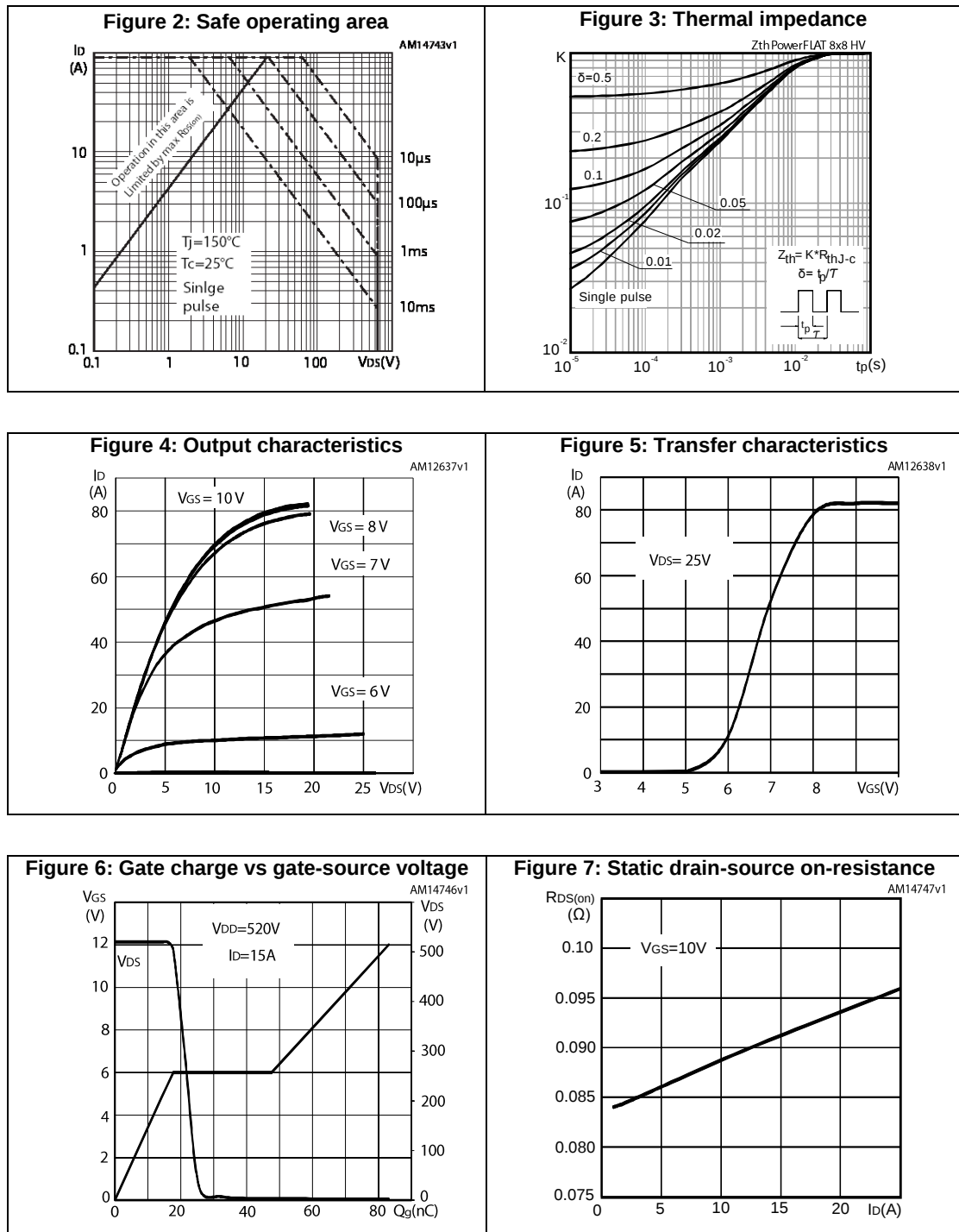


Figure 8: Capacitance variations

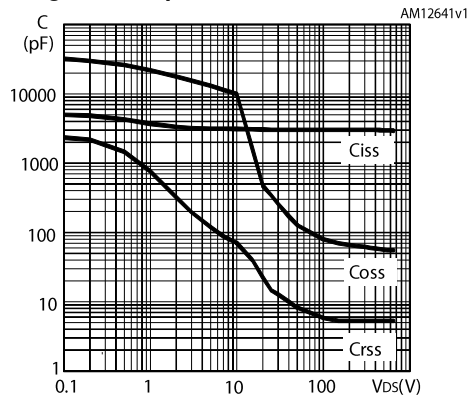


Figure 9: Normalized gate threshold voltage vs temperature

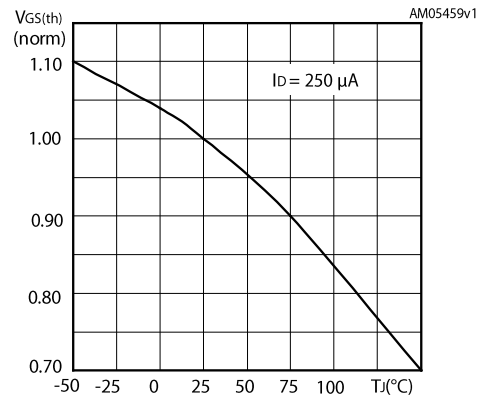


Figure 10: Normalized on-resistance vs temperature

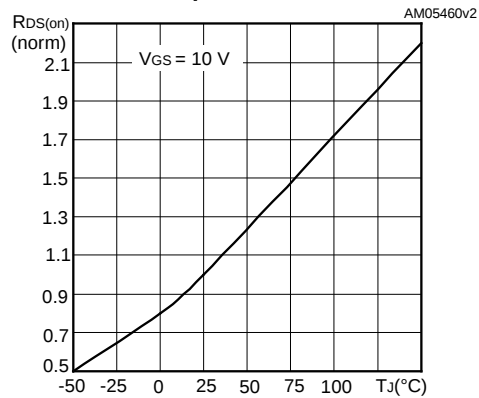


Figure 11: Normalized V(BR)DSS vs temperature

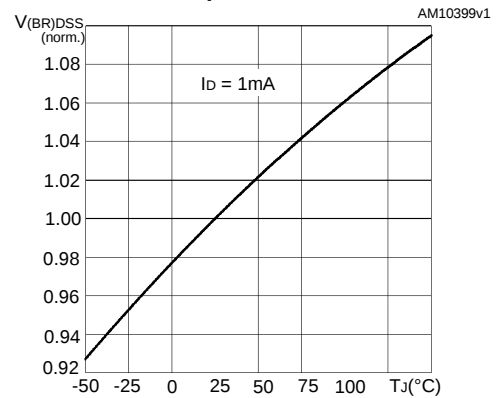


Figure 12: Output capacitance stored energy

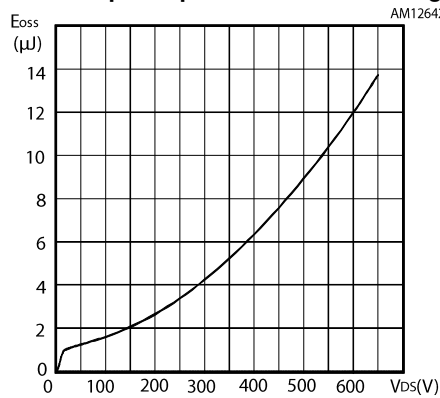


Figure 13: Source-drain diode forward characteristics

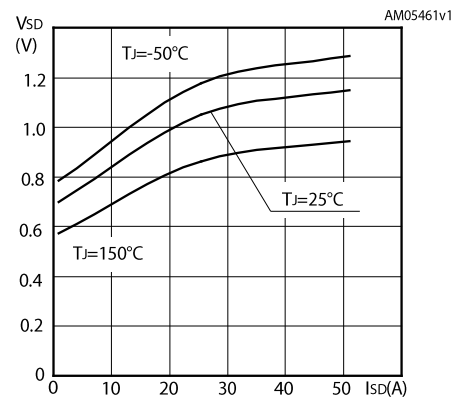
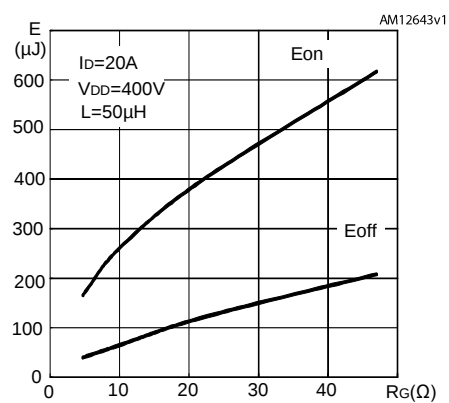


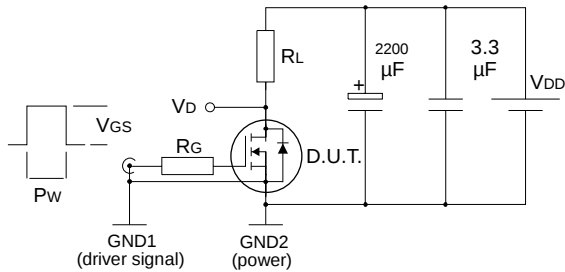
Figure 14: Switching losses vs gate resistance



The previous figure E_{on} includes reverse recovery of a SiC diode.

3 Test circuits

Figure 15: Switching times test circuit for resistive load



AM15855v1

Figure 16: Gate charge test circuit

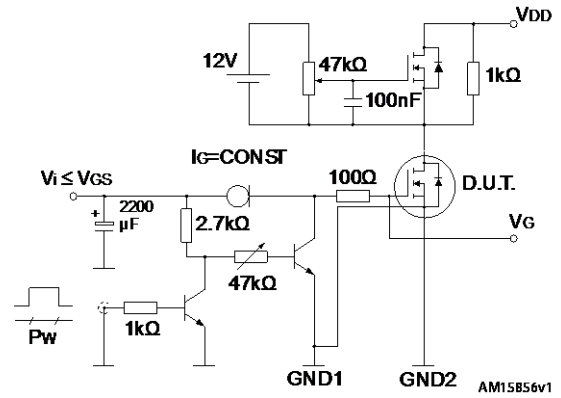
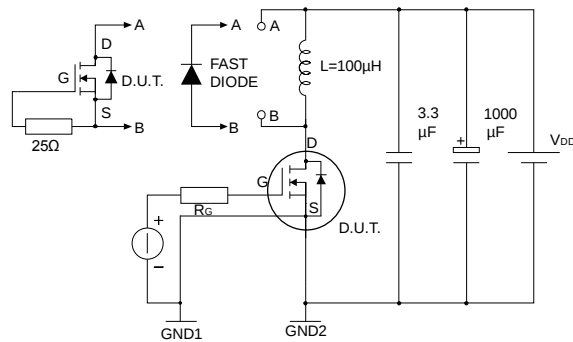
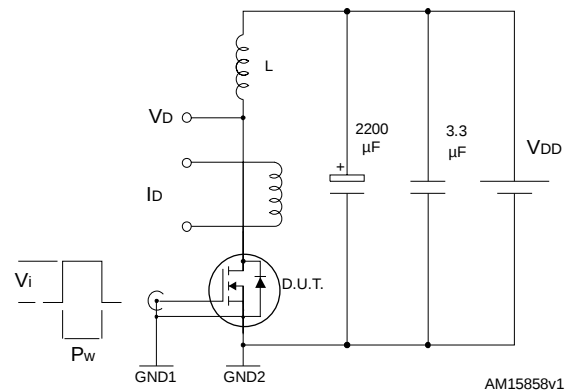


Figure 17: Test circuit for inductive load switching and diode recovery times



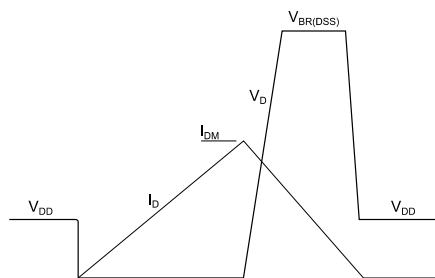
AM15857v1

Figure 18: Unclamped inductive load test circuit



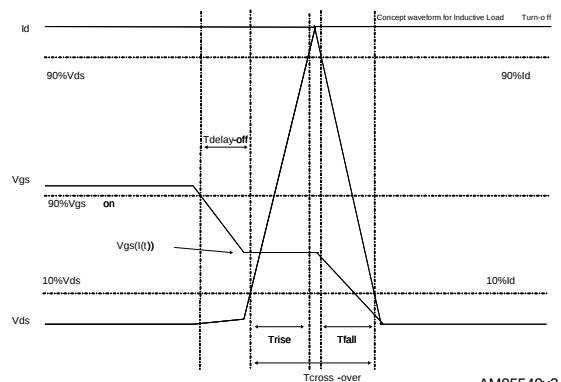
AM15858v1

Figure 19: Unclamped inductive waveform



AM01472v1

Figure 20: Switching time waveform



AM05540v2

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK® is an ST trademark.

4.1 PowerFLAT™ 8x8 HV package information

Figure 21: PowerFLAT™ 8x8 HV drawing

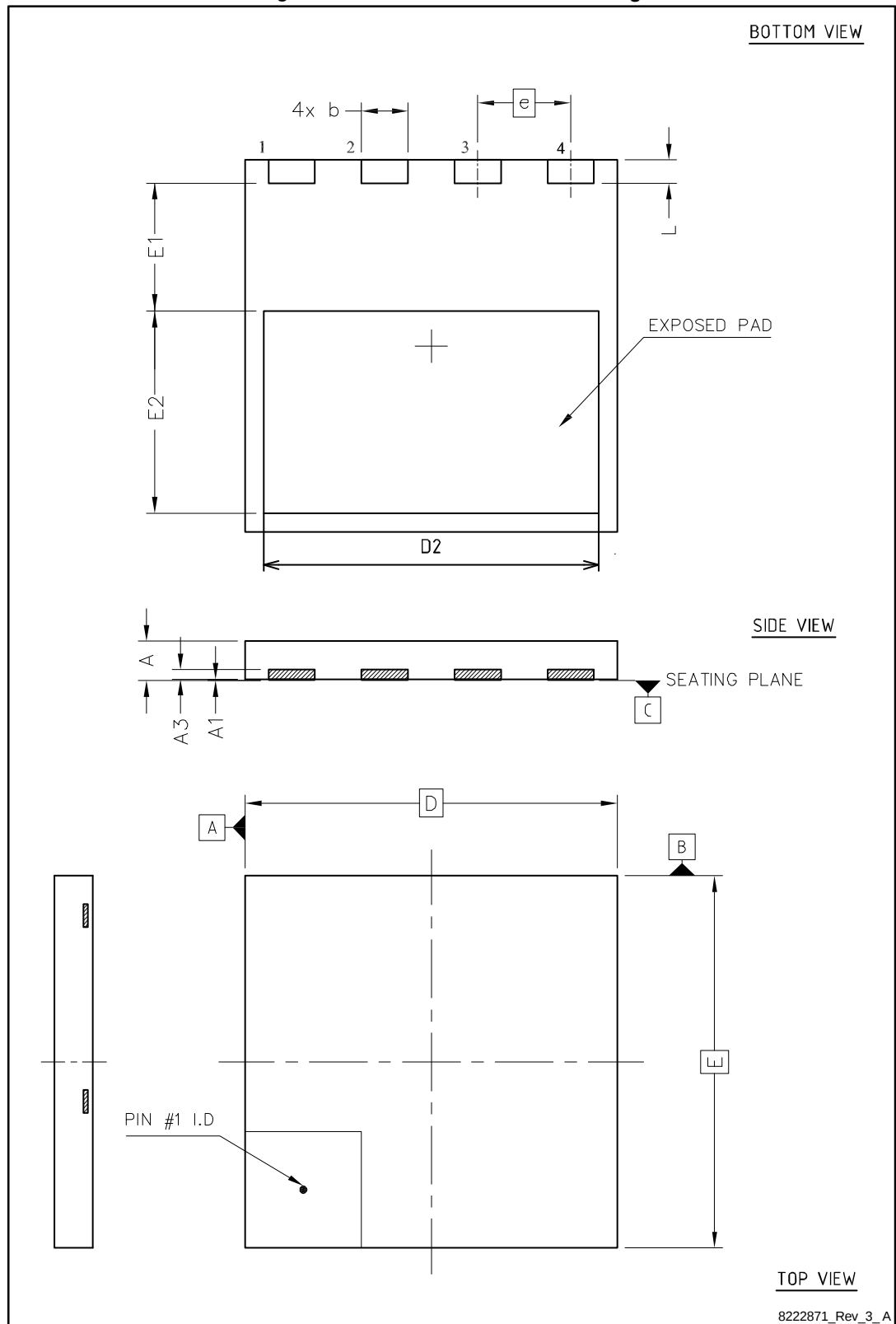
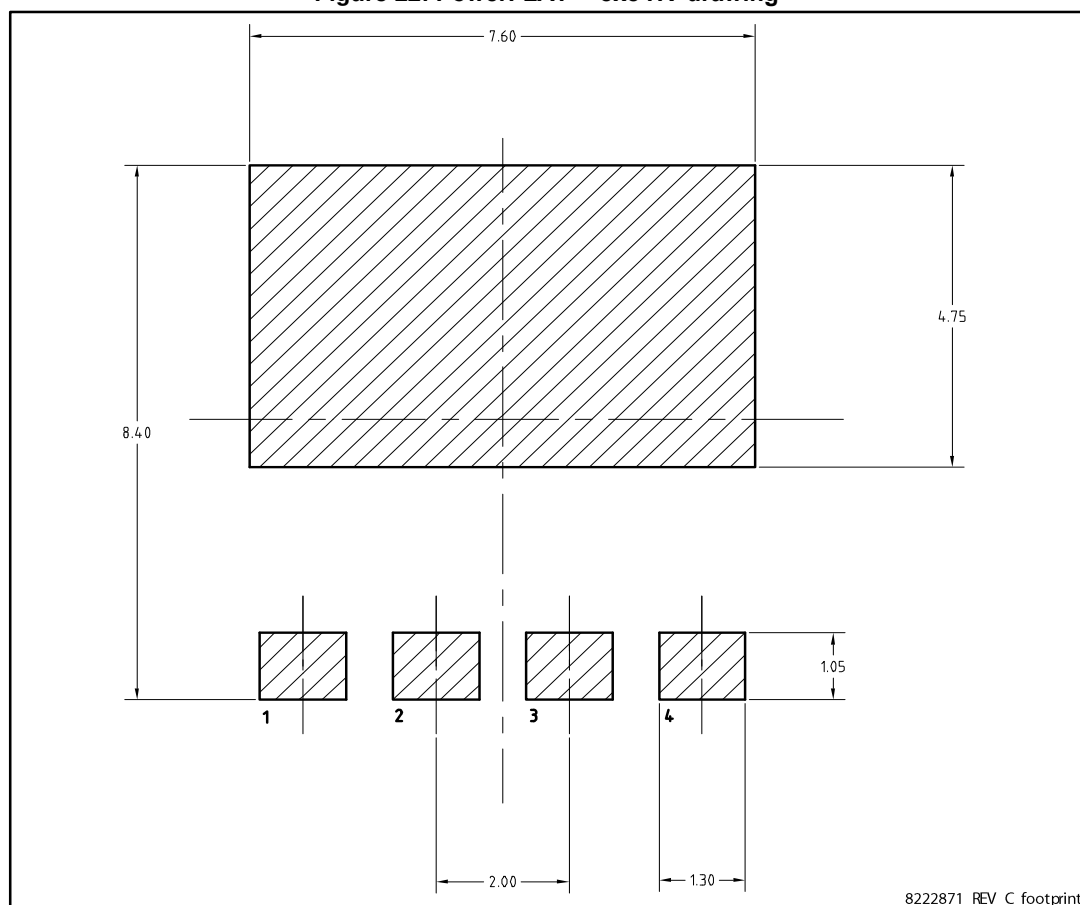


Table 8: PowerFLAT™ 8x8 HV mechanical data

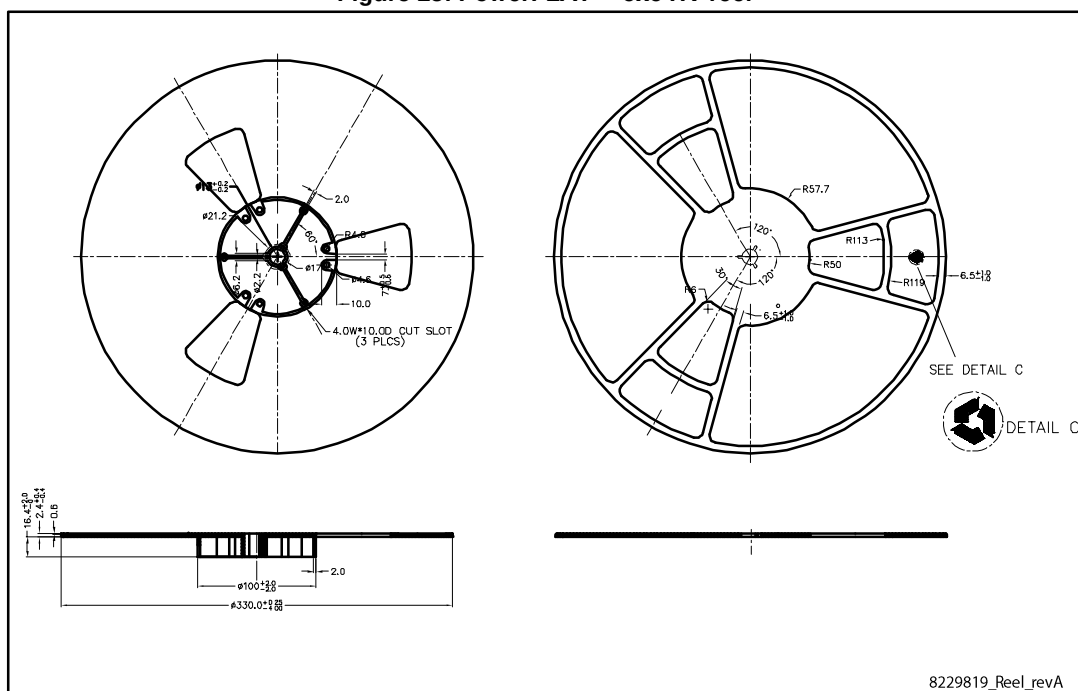
Dim.	mm		
	Min.	Typ.	Max.
A	0.75	0.85	0.95
A1	0.00		0.05
A3	0.10	0.20	0.30
b	0.90	1.00	1.10
D	7.90	8.00	8.10
E	7.90	8.00	8.10
D2	7.10	7.20	7.30
E1	2.65	2.75	2.85
E2	4.25	4.35	4.45
e		2.00	
L	0.40	0.50	0.60

Figure 22: PowerFLAT™ 8x8 HV drawing



All the dimensions are in millimeters.

Figure 25: PowerFLAT™ 8x8 HV reel



5 Revision history

Table 9: Document revision history

Date	Revision	Changes
17-Jan-2013	1	First release.
27-Aug-2015	2	Updated title, features, internal schematic and description on cover page. Document status promoted from preliminary to production data. Updated package information. Minor text changes.

IMPORTANT NOTICE – PLEASE READ CAREFULLY

STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers' products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2015 STMicroelectronics – All rights reserved